



IRFB4620PBF Information

Part Number IRFB4620PBF

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 200V 25A TO-220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com

E-mail: salesdept@heisener.com



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IRFB4620PBF Specifications

Manufacturer Part Number IRFB4620PBF Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 200V Current - Continuous Drain (Id) @ 25°C 25A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 100µA Gate Charge (Qg) (Max) @ Vgs 38nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1710pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 144W (Tc) Rds On (Max) @ Id, Vgs 72.5 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C25A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 100μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1710pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)144W (Tc)Rds On (Max) @ Id, Vgs72.5 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)200VCurrent - Continuous Drain (Id) @ 25°C25A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 100μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1710pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)144W (Tc)Rds On (Max) @ Id, Vgs72.5 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Series	HEXFET?
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Current - Continuous Drain (Id) @ 25°C25A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 100μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1710pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)144W (Tc)Rds On (Max) @ Id, Vgs72.5 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 100μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1710pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)144W (Tc)Rds On (Max) @ Id, Vgs72.5 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Drain to Source Voltage (Vdss)	200V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB	Current - Continuous Drain (Id) @ 25°C	25A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1710pF @ 50V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 72.5 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) E20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 72.5 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	5V @ 100μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)144W (Tc)Rds On (Max) @ Id, Vgs72.5 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	38nC @ 10V
FET Feature - Power Dissipation (Max) 144W (Tc) Rds On (Max) @ Id, Vgs 72.5 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	1710pF @ 50V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 72.5 mOhm @ 15A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs72.5 mOhm @ 15A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	144W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	72.5 mOhm @ 15A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
-	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

IRFB4620PBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFB4620PBF Payment Methods





















IRFB4620PBF Shipping Methods













If you have any question about IRFB4620PBF, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com